

SNOS013E - SEPTEMBER 1997 - REVISED MARCH 2013

LMC6442 Dual Micropower Rail-to-Rail Output Single Supply Operational Amplifier

Check for Samples: LMC6442

FEATURES

- (Typical, V_S = 2.2V)
- Output Swing to Within 30 mV of Supply Rail
- High Voltage Gain 103 dB
- Gain Bandwidth Product 9.5 KHz
- Ensured for: 2.2V, 5V, 10V
- Low Supply Current 0.95 µA/Amplifier
- Input Voltage Range -0.3V to V⁺ -0.9V
- 2.1 µW/Amplifier Power Consumption
- Stable for $A_V \ge +2$ or $A_V \le -1$

APPLICATIONS

- Portable Instruments
- Smoke/Gas/CO/Fire Detectors
- Pagers/Cell Phones
- Instrumentation
- Thermostats
- Occupancy Sensors
- Cameras
- Active Badges

DESCRIPTION

The LMC6442 is ideal for battery powered systems, where very low supply current (less than one microamp per amplifier) and Rail-to-Rail output swing is required. It is characterized for 2.2V to 10V operation, and at 2.2V supply, the LMC6442 is ideal for single (Li-Ion) or two cell (NiCad or alkaline) battery systems.

The LMC6442 is designed for battery powered systems that require long service life through low supply current, such as smoke and gas detectors, and pager or personal communications systems.

Operation from single supply is enhanced by the wide common mode input voltage range which includes the ground (or negative supply) for ground sensing applications. Very low (5 fA, typical) input bias current and near constant supply current over supply voltage enhance the LMC6442's performance near the endof-life battery voltage.

Designed for closed loop gains of greater than plus two (or minus one), the amplifier has typically 9.5 KHz GBWP (Gain Bandwidth Product). Unity gain can be used with a simple compensation circuit, which also allows capacitive loads of up to 300 pF to be driven, as described in the Application Information section.

Connection Diagram

 B
 V⁺

 -IN A
 2
 7
 OUT B

 +IN A
 3
 6
 -IN B

 V⁻
 4
 5
 +IN B

Figure 1. 8-Pin SOIC / PDIP Package See Package Numbers D0008A, P0008E

NE CON

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

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Absolute Maximum Ratings ⁽¹⁾⁽²⁾

ESD Tolerance ⁽³⁾	2 kV
Differential Input Voltage	±Supply Voltages
Voltage at Input/Output Pin	(V ⁺) + 0.3V, (V [−]) − 0.3V
Supply Voltage (V ⁺ – V ⁻):	16V
Current at Input Pin ⁽⁴⁾	±5 mA
Current at Output Pin ⁽⁵⁾ ⁽⁶⁾	±30 mA
Lead Temp. (soldering 10 sec)	260°C
Storage Temp. Range:	−65°C to +150°C
Junction Temp. ⁽⁷⁾	150°C

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.

- If Military/Aerospace specified devices are required, please contact the TI Sales Office/ Distributors for availability and specifications.
- Human body model, 1.5 k Ω in series with 100 pF. (3)
- (4) Limiting input pin current is only necessary for input voltages that exceed absolute maximum input voltage ratings.
- (5) Applies to both single-supply and split-supply operation. Continuous short circuit operation at elevated ambient temperature can result in exceeding the maximum allowed junction temperature of 150°C. Output currents in excess of ±30 mA over long term may adversely affect reliability.
- (6)
- Do not short circuit output to V⁺, when V⁺ is greater than 13V or reliability will be adversely affected. The maximum power dissipation is a function of $T_{J(MAX)}$, θ_{JA} , and T_A . The maximum allowable power dissipation at any ambient temperature is $P_D = (T_{J(MAX)} T_A)/\theta_{JA}$. All numbers apply for packages soldered directly into a PC board. (7)

Operating Ratings ⁽¹⁾

Supply Voltage		$1.8V \le V_S \le 11V$		
Junction Temperature Rang	ge: LMC6442AI, LMC6442I	−40°C < T _J < +85		
Thermal Resistance (θ_{JA})	D0008A Package, 8-pin Surface Mount	193°C/W		
	P0008E Package, 8-pin Molded DIP	115°C/W		

Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for (1) which the device is intended to be functional, but specific performance is not ensured. For ensured specifications and the test conditions, see the Electrical Characteristics.

2.2V Electrical Characteristics

Unless otherwise specified, all limits ensured for $T_J = 25^{\circ}C$, $V^+ = 2.2V$, $V^- = 0V$, $V_{CM} = V_0 = V^+/2$, and $R_L = 1 \text{ M}\Omega$ to $V^+/2$. Boldface limits apply at the temperature extremes.

	Parameter	Parameter Test Conditions		LMC6442AI Limit ⁽²⁾	LMC6442I Limit ⁽²⁾	Units	
DC Elect	trical Characteristics		ł	•	•	*	
V _{OS}	Input Offset Voltage		-0.75	±3 ±4	±7 ±8	mV max	
TCV _{OS}	Temp. coefficient of input offset voltage		0.4			μV/°C	
Ι _Β	Input Bias Current	See ⁽³⁾	0.005	4	4	pA max	
I _{OS}	Input Offset Current	See ⁽³⁾	0.0025	2	2	pA max	
CMRR	Common Mode Rejection Ratio	$-0.1V \le V_{CM} \le 0.5V$	92	67 67	67 67	dB min	
C _{IN}	Common Mode Input Capacitance		4.7			pF	
PSRR	Power Supply Rejection Ratio	$V_{\rm S} = 2.5 \text{ V to } 10 \text{ V}$	95	75 75	75 75	dB min	

Typical Values represent the most likely parametric norm. (1)

(2) All limits are specified by testing or statistical analysis unless otherwise specified.

(3)Limits specified by design.



2.2V Electrical Characteristics (continued)

Unless otherwise specified, all limits ensured for $T_J = 25^{\circ}C$, $V^+ = 2.2V$, $V^- = 0V$, $V_{CM} = V_0 = V^+/2$, and $R_L = 1 \text{ M}\Omega$ to $V^+/2$. Boldface limits apply at the temperature extremes.

	Parameter	Test Conditions	Тур ⁽¹⁾	LMC6442AI Limit ⁽²⁾	LMC6442I Limit ⁽²⁾	Units
V _{CM}	Input Common-Mode Voltage Range	CMRR ≥ 50 dB	1.3	1.05 0.95	1.05 0.95	V min
		CIVIRR 2 50 0B	-0.3	-0.2 0	-0.2 0	V max
A _V	Large Signal Voltage Gain	Sourcing ⁽⁴⁾	100			
		Sinking ⁽⁴⁾	94			dB min
		$V_{O} = 0.22V$ to 2V	103	80	80	
Vo	Output Swing	$V_{ID} = 100 \text{ mV}^{(5)}$	2.18	2.15 2.15	2.15 2.15	V min
	$V_{ID} = -100 \text{ mV}^{(5)}$	22	60 60	60 60	mV max	
I _{SC}	Output Short Circuit Current	Sourcing, V_{ID} = 100 mV ⁽⁶⁾ ⁽⁵⁾	50	18 17	18 17	μA
		Sinking, $V_{ID} = -100 \text{ mV}^{(6)}$ (5)	50	20 19	20 19	min
I _S	Supply Current (2 amplifiers)	R _L = open	1.90	2.4 3.0	2.6 3.2	μA
		V ⁺ = 1.8V, R _L = open	2.10			max
AC Elec	trical Characteristics					
SR	Slew Rate (7)		2.2			V/ms
GBWP	Gain-Bandwidth Product		9.5			KHz
φ _m	Phase Margin	See ⁽⁸⁾	63			deg

(4) R_L connected to V⁺/2. For Sourcing Test, V_O > V⁺/2. For Sinking tests, V_O < V⁺/2.
(5) V_{ID} is differential input voltage referenced to inverting input.
(6) Output shorted to ground for sourcing, and shorted to V+ for sinking short circuit current test.

(7) Slew rate is the slower of the rising and falling slew rates.

See the Typical Performance Characteristics and Applications Information sections for more details. (8)

5V Electrical Characteristics

Unless otherwise specified, all limits ensured for $T_J = 25^{\circ}C$, $V^+ = 5V$, $V^- = 0V$, $V_{CM} = V_0 = V^{+/2}$, and $R_L = 1 \text{ M}\Omega$ to $V^{+/2}$. Boldface limits apply at the temperature extremes.

	Parameter Test Conditions		Тур ⁽¹⁾	LMC6442AI Limit ⁽²⁾	LMC6442I Limit ⁽²⁾	Units
DC Elect	rical Characteristics	-				
V _{OS}	Input Offset Voltage		-0.75	±3 ±4	±7 ±8	mV max
TCV _{OS}	Temp. coefficient of input offset voltage		0.4			µV/°C
I _B	Input Bias Current	See ⁽³⁾	0.005	4	4	pA max
I _{OS}	Input Offset Current	See ⁽³⁾	0.0025	2	2	pA max
CMRR	Common Mode Rejection Ratio	$-0.1V \le V_{CM} \le 3.5V$	102	70 70	70 70	dB min
C _{IN}	Common Mode Input Capacitance		4.1			pF
PSRR	Power Supply Rejection Ratio	V _S = 2.5 V to 10V	95	75 75	75 75	dB min

(1) Typical Values represent the most likely parametric norm.

(2) All limits are specified by testing or statistical analysis unless otherwise specified.

Limits specified by design. (3)

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5V Electrical Characteristics (continued)

Unless otherwise specified, all limits ensured for $T_J = 25^{\circ}C$, $V^+ = 5V$, $V^- = 0V$, $V_{CM} = V_O = V^+/2$, and $R_L = 1 \text{ M}\Omega$ to $V^+/2$. Boldface limits apply at the temperature extremes.

	Parameter	Test Conditions	Тур ⁽¹⁾	LMC6442AI Limit ⁽²⁾	LMC6442I Limit ⁽²⁾	Units
V _{CM}	Input Common-Mode Voltage Range	CMRR ≥ 50 dB	4.1	3.85 3.75	3.85 3.75	V min
		CMRR 2 50 0B	-0.4	-0.2 0	-0.2 0	V max
A _V	Large Signal Voltage Gain	Sourcing ⁽⁴⁾	100			
		Sinking ⁽⁴⁾	94			dB min
		$V_{O} = 0.5V$ to 4.5V	103	80	80	
Vo	Output Swing	$V_{ID} = 100 \text{ mV}^{(5)}$	4.99	4.95 4.95	4.95 4.95	V min
	$V_{ID} = -100 \text{ mV}^{(5)}$	20	50 50	50 50	mV max	
I _{SC}	Output Short Circuit Current	Sourcing, V_{ID} = 100 mV ⁽⁶⁾ ⁽⁵⁾	500	300 200	300 200	μA
		Sinking, $V_{ID} = -100 \text{ mV}^{(6)}$ ⁽⁵⁾	350	200 150	200 150	min
I _S	Supply Current (2 amplifiers)	R _L = open	1.90	2.4 3.0	2.6 3.2	μA max
AC Elect	rical Characteristics	•		•		-
SR	Slew Rate (7)		4.1	2.5	2.5	V/ms
GBWP	Gain-Bandwidth Product		10			KHz
φ _m	Phase Margin	See ⁽⁸⁾	64			deg
THD	Total Harmonic Distortion	$\begin{array}{l} A_{V}=+2,f=100~Hz,\\ R_{L}=10~M\Omega,V_{OUT}=1~V_{PP} \end{array}$	0.08			%

(4) R_L connected to V⁺/2. For Sourcing Test, V_O > V⁺/2. For Sinking tests, V_O < V⁺/2. (5) V_{ID} is differential input voltage referenced to inverting input.

(6) Output shorted to ground for sourcing, and shorted to V+ for sinking short circuit current test.

(7) Slew rate is the slower of the rising and falling slew rates.

(8) See the Typical Performance Characteristics and Applications Information sections for more details.

10V Electrical Characteristics

Unless otherwise specified, all limits ensured for $T_J = 25^{\circ}$ C, V⁺ = 10V, V⁻ = 0V, V_{CM} = V_O = V ⁺/2, and R_L = 1 M Ω to V⁺/2. Boldface limits apply at the temperature extremes.

	Parameter	Parameter Test Conditions		LMC6442AI Limit ⁽²⁾	LMC6442I Limit ⁽²⁾	Units	
DC Elect	rical Characteristics						
V _{OS}	Input Offset Voltage	e -1.5 ±3 ±4		±7 ±8	mV max		
TCV _{OS}	Temp. coefficient of input offset voltage		0.4			µV/°C	
I _B	Input Bias Current	See ⁽³⁾	0.005	4	4	pA max	
I _{OS}	Input Offset Current	See ⁽³⁾	0.0025	2	2	pA max	
CMRR	Common Mode Rejection Ratio	$-0.1V \le V_{CM} \le 8.5V$	105	70 70	70 70	dB min	
C _{IN}	Common Mode Input Capacitance		3.5			pF	
PSRR	Power Supply Rejection Ratio	V _S = 2.5 V to 10V	95	75 75	75 75	dB min	

Typical Values represent the most likely parametric norm. (1)

(2) All limits are specified by testing or statistical analysis unless otherwise specified.

(3) Limits specified by design.



10V Electrical Characteristics (continued)

Unless otherwise specified, all limits ensured for $T_J = 25^{\circ}C$, $V^+ = 10V$, $V^- = 0V$, $V_{CM} = V_O = V^+/2$, and $R_L = 1 \text{ M}\Omega$ to $V^+/2$. Boldface limits apply at the temperature extremes.

	Parameter	Test Conditions	Тур ⁽¹⁾	LMC6442AI Limit ⁽²⁾	LMC6442I Limit ⁽²⁾	Units
V_{CM}	Input Common-Mode Voltage Range	CMRR ≥ 50 dB	9.1	8.85 8.75	8.85 8.75	V min
			-0.4	-0.2 0	-0.2 0	V max
A _V	Large Signal Voltage Gain	Sourcing ⁽⁴⁾	120			
		Sinking (4)	100			dB min
		$V_{O} = 0.5V$ to 9.5V	104	80	80	
Vo	Output Swing	$V_{ID} = 100 \text{ mV}^{(5)}$	9.99	9.97 9.97	9.97 9.97	V min
		$V_{ID} = -100 \text{ mV}^{(5)}$	22	50 50	50 50	mV max
I _{SC}	SC Output Short Circuit Current	Sourcing, V_{ID} = 100 mV ⁽⁶⁾ ⁽⁵⁾	2100	1200 1000	1200 1000	μA
		Sinking, $V_{ID} = -100 \text{ mV}^{(6)}$ (5)	900	600 500	600 500	min
I _S	Supply Current (2 amplifiers)	R _L = open	1.90	2.4 3.0	2.6 3.2	μA max
AC Elect	trical Characteristics	•	•	-	•	
SR	Slew Rate ⁽⁷⁾		4.1	2.5	2.5	V/ms
GBWP	Gain-Bandwidth Product		10.5			KHz
φ _m	Phase Margin	See ⁽⁸⁾	68			deg
e _n	Input-Referred Voltage Noise	R _L = open f = 10 Hz	170			nV/√Hz
i _n	Input-Referred Current Noise	R _L = open f = 10 Hz	0.0002			pA/√Hz
	Crosstalk Rejection	See ⁽⁹⁾	85			dB

(4)

(5)

 R_L connected to V⁺/2. For Sourcing Test, $V_O > V^+/2$. For Sinking tests, $V_O < V^+/2$. V_{ID} is differential input voltage referenced to inverting input. Output shorted to ground for sourcing, and shorted to V+ for sinking short circuit current test. Slew rate is the slower of the rising and falling slew rates. (6)

(7)

(8)

See the Typical Performance Characteristics and Applications Information sections for more details. Input referred, $V^+ = 10V$ and $R_L = 10 M\Omega$ connected to 5V. Each amp excited in turn with 1 KHz to produce about 10 V_{PP} output. (9)

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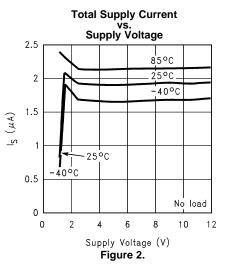
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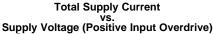
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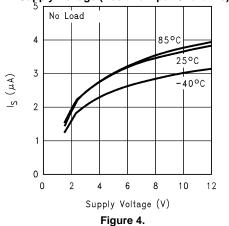
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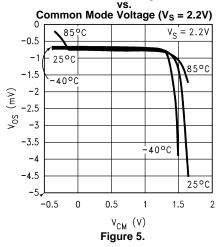
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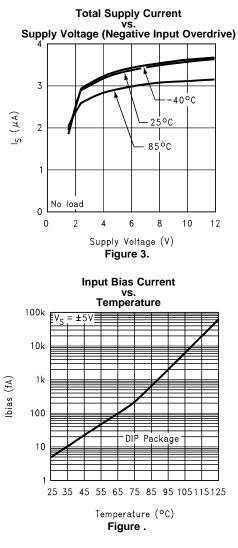


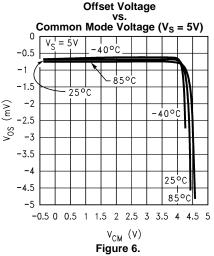












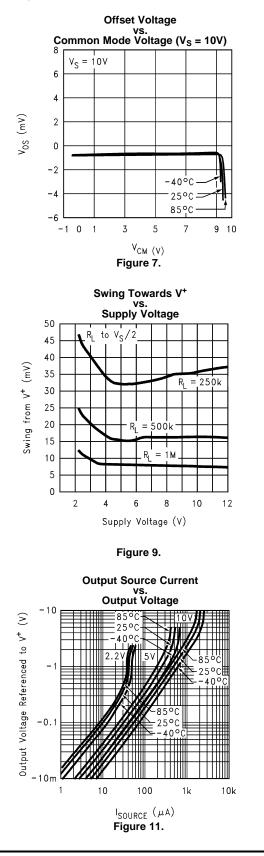
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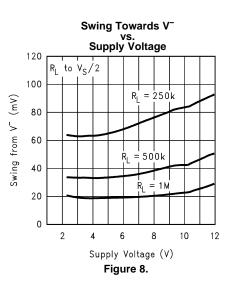


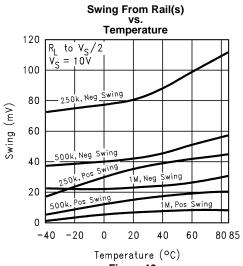
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Typical Performance Characteristics (continued)

 $V_{S} = 5V$, Single Supply, $T_{A} = 25^{\circ}C$ unless otherwise specified

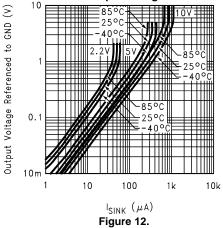








Output Sink Current vs. Output Voltage



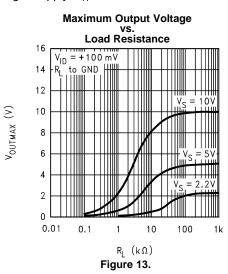
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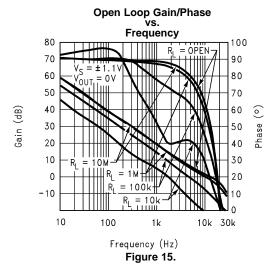
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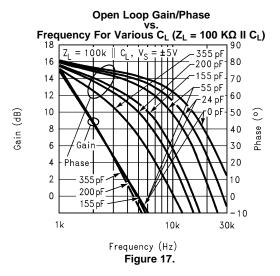
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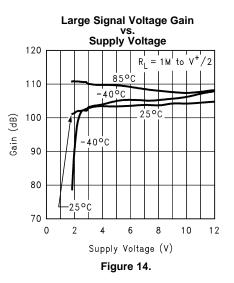


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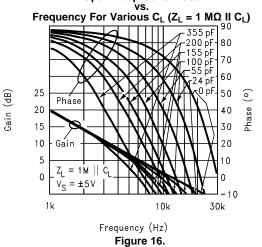








Open Loop Gain/Phase



Gain Bandwidth Product vs. Supply Voltage 16 R_{L} to $V^{+}/2$ _V_{OUT} = V /2 = 10MR 14 12 RL = 1 M 10 8 6 = 100k RL 1 2 3 4 5 6 78 9 10 11 12 Supply Voltage (V) Figure 18.

GBWP (kHz)

8



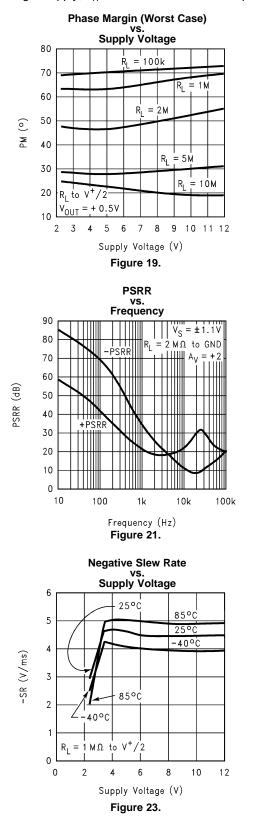
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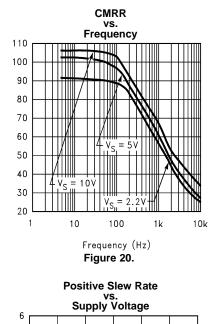
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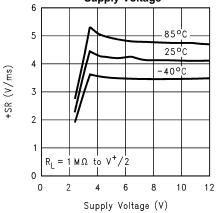
Typical Performance Characteristics (continued)

CMRR (dB)

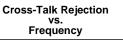
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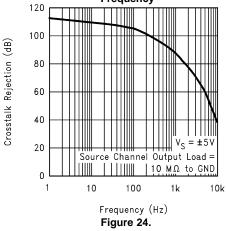








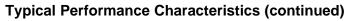




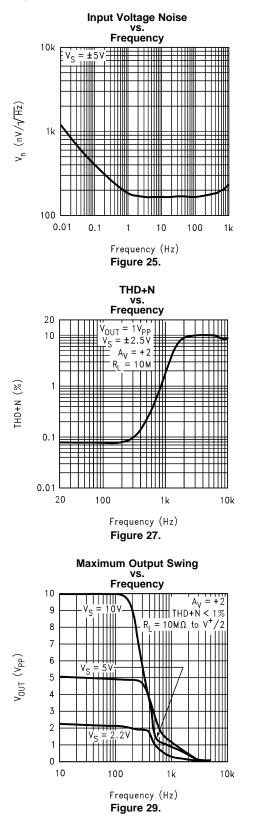
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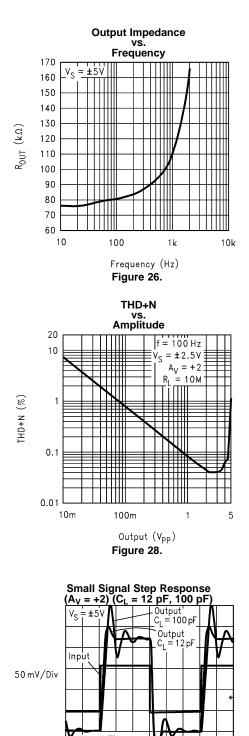
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 V_{S} = 5V, Single Supply, T_{A} = 25°C unless otherwise specified





200 µs/Div

Figure 30.

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 $C_L = 12 \, \text{pF}$

C_L = 100 pF

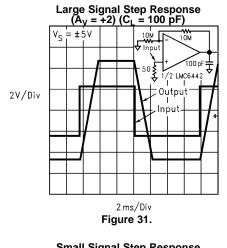


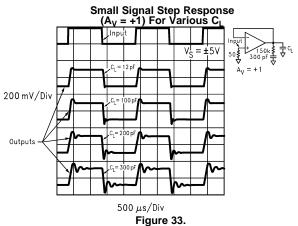
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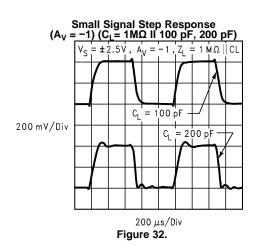
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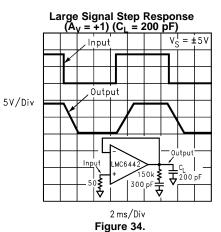
Typical Performance Characteristics (continued)

 $V_{\rm S}$ = 5V, Single Supply, $T_{\rm A}$ = 25°C unless otherwise specified









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ISTRUMENTS

APPLICATIONS INFORMATION

USING LMC6442 IN UNITY GAIN APPLICATIONS

LMC6442 is optimized for maximum bandwidth and minimal external components when operating at a minimum closed loop gain of +2 (or -1). However, it is also possible to operate the device in a unity gain configuration by adding external compensation as shown in Figure 35:

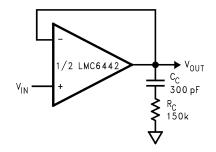


Figure 35. $A_V = +1$ Operation by adding C_C and R_C

Using this compensation technique it is possible to drive capacitive loads of up to 300 pF without causing oscillations (see the Typical Performance Characteristics for step response plots). This compensation can also be used with other gain settings in order to improve stability, especially when driving capacitive loads (for optimum performance, R_C and C_C may need to be adjusted).

USING "T" NETWORK

Compromises need to be made whenever high gain inverting stages need to achieve a high input impedance as well. This is especially important in low current applications which tend to deal with high resistance values. Using a traditional inverting amplifier, gain is inversely proportional to the resistor value tied between the inverting terminal and input while the input impedance is equal to this value. For example, in order to build an inverting amplifier with an input impedance of $10M\Omega$ and a gain of 100, one needs to come up with a feedback resistor of $1000 M\Omega$ -an expensive task.

An alternate solution is to use a "T" Network in the feedback path, as shown in Figure 36.

Closed loop gain, A_V is given by:

$$A_{V} = -\frac{R^{2}}{R2} \bullet \left(\frac{2}{R} + \frac{1}{R1}\right)$$

$$(1)$$

$$V_{IN} \bigcirc V_{IN} \bigcirc$$

Figure 36. "T" Network Used to Replace High Value Resistor

It must be noted, however, that using this scheme, the realizable bandwidth would be less than the theoretical maximum. With feedback factor, β , defined as:

$$\beta \approx \frac{R2}{R2 + R} \bullet \frac{R1}{R1 + R} \text{ for } R2 \gg R1$$

$$BW(-3 \ dB) \approx GBWP \bullet \beta$$
(2)
(3)

In this case, assuming a GBWP of about 10 KHz, the expected BW would be around 50 Hz (vs. 100 Hz with the conventional inverting amplifier).



(4)

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Looking at the problem from a different view, with R_F defined by A_V •Rin, one could select a value for R in the "T" Network and then determine R1 based on this selection:

$$R1 = \frac{R^2}{R_F - 2R}$$

(U) U 10k 10k

Figure 37. "T" Network Values for Various Values of R

For convenience, Figure 37 shows R1 vs. R_F for different values of R.

DESIGN CONSIDERATIONS FOR CAPACITIVE LOADS

As with many other opamps, the LMC6442 is more stable at higher closed loop gains when driving a capacitive load. Figure 38 shows minimum closed loop gain versus load capacitance, to achieve less than 10% overshoot in the output small signal response. In addition, the LMC6442 is more stable when it provides more output current to the load and when its output voltage does not swing close to V⁻.

The LMC6442 is more tolerant to capacitive loads when the equivalent output load resistance is lowered or when output voltage is 1V or greater from the V⁻ supply. The capacitive load drive capability is also improved by adding an isolating resistor in series with the load and the output of the device. Figure 39 shows the value of this resistor for various capacitive loads ($A_V = -1$), while limiting the output to less than 10 % overshoot.

Referring to the Typical Performance Characteristics plot of Phase Margin (Worst Case) vs. Supply Voltage, note that Phase Margin increases as the equivalent output load resistance is lowered. This plot shows the expected Phase Margin when the device output is very close to V⁻, which is the least stable condition of operation. Comparing this Phase Margin value to the one read off the Open Loop Gain/Phase vs. Frequency plot, one can predict the improvement in Phase Margin if the output does not swing close to V⁻. This dependence of Phase Margin on output voltage is minimized as long as the output load, R_L , is about 1M Ω or less.

Output Phase Reversal: The LMC6442 is immune against this behavior even when the input voltages exceed the common mode voltage range.

Output Time Delay: Due to the ultra low power consumption of the device, there could be as long as 2.5 ms of time delay from when power is applied to when the device output reaches its final value.



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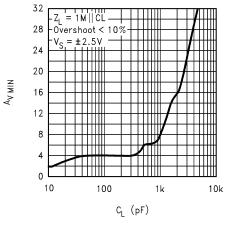


Figure 38. Minimum Operating Gain vs. Capacitive Load

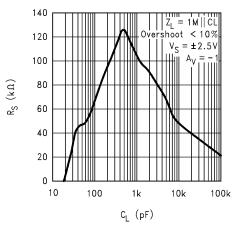


Figure 39. Isolating Resistor Value vs Capacitive Load

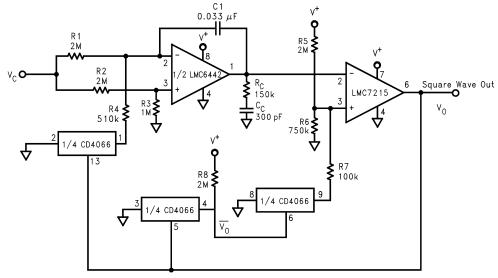


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V ⁺ = 5V: $I_S < 10 \ \mu A$, f/V_C = 4.3 (Hz/V)

$$R1 \cong 4R4$$

$$f(Hz) = \frac{V_{C}}{3R_{1}C_{1}V^{+}\left[\frac{R6}{R5+R6} - \frac{(R6 \parallel R7)}{(R6 \parallel R7)+R5}\right]} \cong \frac{V_{C}(R5+R6)}{3R_{1}C_{1}V^{+}(R6-R7)} \text{ for } R5 >> R6 \text{ and } R6 >> R7$$

Figure 40. Micropower Single Supply Voltage to Frequency Converter

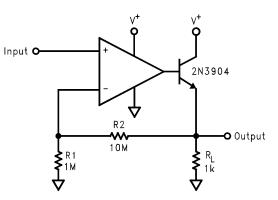
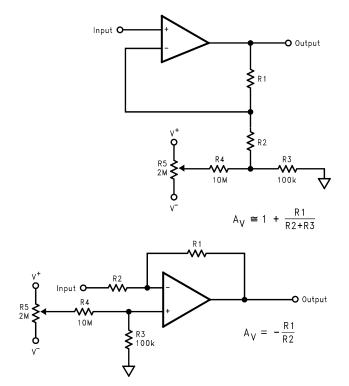


Figure 41. Gain Stage with Current Boosting

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REVISION HISTORY

Ch	nanges from Revision D (March 2013) to Revision E	Page
•	Changed layout of National Data Sheet to TI format	. 16



PACKAGING INFORMATION

Orderable Device	Status	Package Type	•	Pins	Package	Eco Plan	Lead finish/	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	Ball material	(3)		(4/5)	
							(6)				
LMC6442AIM/NOPB	ACTIVE	SOIC	D	8	95	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	LMC64 42AIM	Samples
LMC6442AIMX/NOPB	ACTIVE	SOIC	D	8	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	LMC64 42AIM	Samples
LMC6442IM/NOPB	ACTIVE	SOIC	D	8	95	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	LMC64 42IM	Samples
LMC6442IMX/NOPB	ACTIVE	SOIC	D	8	2500	RoHS & Green	Call TI SN	Level-1-260C-UNLIM	-40 to 85	LMC64 42IM	Samples
LMC6442IN/NOPB	ACTIVE	PDIP	Р	8	40	RoHS & Green	NIPDAU	Level-1-NA-UNLIM	-40 to 85	LMC6442 IN	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.



14-Apr-2022

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMC6442AIMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1
LMC6442IMX/NOPB	SOIC	D	8	2500	330.0	12.4	6.5	5.4	2.0	8.0	12.0	Q1



PACKAGE MATERIALS INFORMATION

11-Feb-2022



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMC6442AIMX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0
LMC6442IMX/NOPB	SOIC	D	8	2500	367.0	367.0	35.0



11-Feb-2022

TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
LMC6442AIM/NOPB	D	SOIC	8	95	495	8	4064	3.05
LMC6442IM/NOPB	D	SOIC	8	95	495	8	4064	3.05
LMC6442IN/NOPB	Р	PDIP	8	40	502	14	11938	4.32

D0008A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



D0008A

EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



D0008A

EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



P(R-PDIP-T8)

PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.



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